

SILICON EPITAXIAL HIGH SPEED SWITCHING DIODE

Features

- · Smal plastic package suitable for surface mounted
- High Speed (Trr = 1.2 ns Typ.)
- · High reliability with high surge current handling capability
- · RoHS compliant package

Applications

· High speed switching

Description

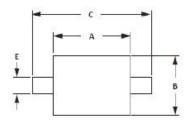
· Silicon planar zener diode in a small plastic SMD SOD-323 package

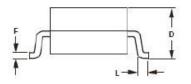
Packing & Order Information

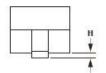
3,000/Reel



RoHS COMPLIANT







OUTLINE DIMENSIONS								
DIM	MILLIMETERS		INCHES					
	MIN	MAX	MIN	MAX				
Α	1.60	1.90	0.063	0.075				
В	1.15	1.45	0.045	0.057				
С	2.39	2.70	0.094	0.106				
D	0.80	1.10	0.031	0.043				
Е	0.25	0.40	0.010	0.016				
F	0.10	0.20	0.004	0.008				
Н	-	0.10		0.004				
L	0.20	-	0.008	-				

NOTES

- Controlling dimension: millimeters.
 Dimensioning and tolerances per ANSI Y14.5M, 1985.
 Dimensions are exclusive of mold flash and metal burrs.

Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)									
Parameter	Symbol	Value	Unit						
Maximum Peak Reverse Voltage	VRRM	90	V						
Maximum DC Reverse Voltage	VRM	80	V						
Maximum Average Forward Current	IF	100	mA						
Maximum Peak Forward Voltage	IFM	255	mA						
Maximum Surge Current (1s)	IFSM	500	mA						
Maximum Junction Temperature	TJ	125	°C						
Storage temperature range	TS	-55 to +175	°C						



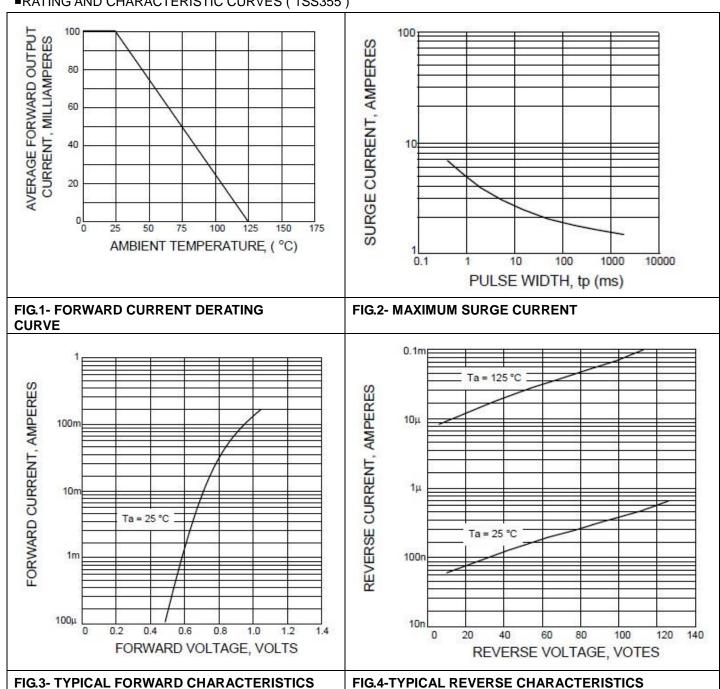
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Electrical characteristics (Tc=25°C unless otherwise noted)										
Parameter	Test Condition	Symbol	Min.	Тур.	Max.	Unit				
Forward Voltage	I _F = 100 mA	VF			1.2	V				
Reverse Current	V _R = 80 V	IR			0.1	μA				
Capacitance between terminals	f = 1MHz ; V _R = 0.5	СТ			3.0	pF				
Davis Davis Time	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$	Т			4.0	ns				
Reverse Recovery Time	R _L = 100 Ω	Trr								



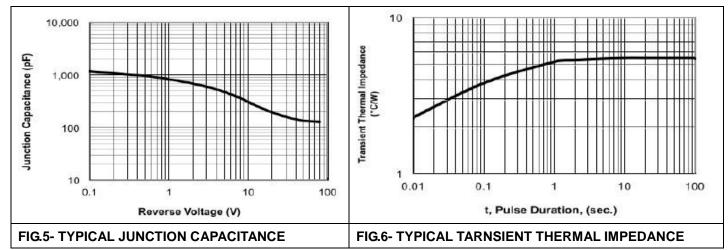
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■RATING AND CHARACTERISTIC CURVES (1SS355)





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